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In the Specification:

Please amend paragraph 28 on page 11 and continuing on page 12 as follows:

[0028] However, GPD has not been used for doping a-Si or poly-Si during formation of a trench structure, such as an inner electrode in a trench capacitor. FIGS. 4A-C illustrate a preferred doping method according to the present invention. FIG. 4A is a cross-sectional view of a trench 402 formed in a semiconductor substrate 400. Certain components (e.g., the buried plate) have been omitted for the sake of clarity. The trench 402 has a depth D, preferably on the order of 6-8  $\mu\text{m}$ . In actuality, the trench 402 is a three-dimensional structure defined by sidewalls [[412]] 410 which may have a cylindrical or other shape. A pad oxide 430 and/or a pad nitride 432 may be formed at the surface of the substrate adjacent to the trench 402. A node dielectric [[420]] 412 lines at least a portion of the sidewalls [[412]] 410. The node dielectric [[420]] 412 may be any suitable dielectric material, preferably having a high dielectric constant, i.e., "high K." As used herein, "high K" materials have a dielectric constant greater than silicon dioxide ( $\text{SiO}_2$ ), which has a dielectric constant of approximately 3.9. By way of example only, one suitable dielectric material is tantalum pentoxide ( $\text{Ta}_2\text{O}_5$ ).